

WHAT IS CLAIMED IS:

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1. A gallium nitride compound semiconductor light emission device comprising:

a substrate;

an n-type electrode region comprising an n-type transmissive electrode;

a gallium nitride compound semiconductor multilayer structure including an active layer; and

a p-type electrode region comprising a p-type transmissive electrode,

wherein the n-type transmissive electrode is of a type which is substantially transparent.

2. A gallium nitride compound semiconductor light emission device according to claim 1, wherein the p-type transmissive electrode and the n-type transmissive electrode transmit light which is generated in the active layer and reflected from the substrate so that the light exits the light emission device.

3. A gallium nitride compound semiconductor light emission device according to claim 1, wherein the n-type transmissive electrode is located outside of the p-type

4. A gallium nitride compound semiconductor light emission device according to claim 1, wherein the n-type transmissive electrode is formed around a circumference of the p-type transmissive electrode.

wherein the gallium nitride compound semiconductor multilayer structure includes a buffer layer and an n-type gallium nitride compound semiconductor layer, and

6. A gallium nitride compound semiconductor light emission device according to claim 1.

wherein the n-type electrode region further comprises an n-type pad electrode, and

wherein the p-type electrode region further comprises a p-type pad electrode.

8. A gallium nitride compound semiconductor light emission device according to claim 6, wherein the p-type pad electrode is formed in the vicinity of a center of a light emitting face of the gallium nitride compound semiconductor light emission device.

10. A gallium nitride compound semiconductor light emission device according to claim 6, wherein the n-type pad electrode is of a type which realizes a Schottky contact.

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